

General Description

The MAX3905 150Mbps automotive VCSEL driver implements low-cost transmitters operating from 8Mbps to 150Mbps at junction temperatures up to +140°C. The device accepts single-ended TTL, differential PECL or LVDS input data, and provides bias and modulation currents for driving a VCSEL. The output is DC-coupled to the VCSEL to minimize component count.

The driver provides temperature compensation to VCSEL high and low currents. Adjustments of the bias current, modulation current, bias-current temperature coefficient, and center of the temperature-stable bias current region are all programmable by wirebond options. The power-reduction feature decreases output modulation by approximately 50%. The data squelch feature disables the VCSEL current when no data is present.

The MAX3905 is available in die form and operates from -40°C to +140°C junction temperature, over a +3.0V to +5.25V supply range.

Applications

Optical Transmitters for Automotive Networks Polymer-Clad Silica Fiber-Based Networks

Features

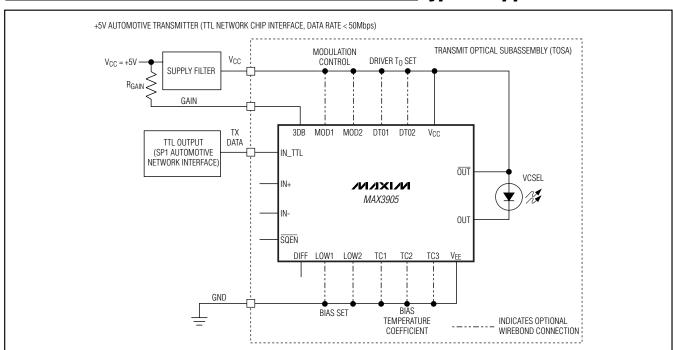
- ♦ -40°C to +140°C Operating Junction Temperature Range
- ♦ +3.0V to +5.25V Supply Voltage
- **♦ TTL/CMOS-, LVDS-, or PECL-Compatible Data**
- ♦ Compatible with SP1 Automotive Network Interface
- ♦ Wirebond-Adjustable VCSEL Low and High Currents
- ♦ Optical Power-Reduction Feature
- ♦ Output Squelch

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX3905E/D	-40°C to +140°C	Dice*

^{*}Dice are designed to operate from $T_{i,j} = -40^{\circ}C$ to $+140^{\circ}C$, but are tested and guaranteed at $T_A = +49^{\circ}C$ only.

Typical Application Circuits



Typical Application Circuits continued at end of data sheet.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, (V _{CC} - V _{EE})	
Voltage at 3DB, IN+, IN-, IN_TTL, DIFF, OUT, OU	Ι,
MOD1, MOD2, DT01, DT02, SQEN,	
TEMPSENS0.5V to	$0 (V_{CC} + 0.5V)$
Voltage at LOW1, LOW2, TC1, TC2, TC3	0.5V to +2V
Differential Input Voltage IIN+ - IN-I	Vcc
Current into OUT	+12mA

Storage Ambient Temperature Range65°C to +	-150°C
Operating Junction Temperature Range40°C to +	·150°C
Electrostatic Discharge (ESD)	
(Human Body Model, tested per JES D22-A114)	2kV
(Machine Model, tested per JES D22-A115)	+400V
Die Attach Temperature+	-400°C
·	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{CC} = +3.0 \text{V to } +5.25 \text{V}, T_J = -40 ^{\circ}\text{C} \text{ to } +140 ^{\circ}\text{C}. \text{ Typical values are at } V_{CC} = +5.0 \text{V and } T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.})$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
OPERATING CONDITIONS						
Voltage at OUT	Vout		0.9			V
Data Rate		With TTL input	8	50		Mbps
Data Hate		With differential input	40		150	IVIDPS
TTL Data Input-Edge Transition Time		One-pole response, 10% to 90%			0.23	UI
POWER SUPPLY	•		'			•
Supply Current	Icc	Excludes I _{OUT} and I _{OUT}		14	25	mA
Supply Current While Data is Squelched	I _{STDBY}	Excludes I _{OUT} and I _{OUT}		14		mA
CURRENT GENERATOR	•		U.			•
		LOW1 open, LOW2 open	1.69	1.8	1.91	mA
Lava Commant (T. DT.)		LOW1 GND, LOW2 open	2.02	2.17	2.28	
Low Current ($T_J = DT_0$)	I _{DT0}	LOW1 open, LOW2 GND	2.35	2.53	2.65	
		LOW1 GND, LOW2 GND	2.68	2.90	3.02	
	TC _{LOW+}	TC1 open, TC2 open, TC3 open	12	16	18	μΑ/°C
Low-Current Positive		TC1 GND, TC2 open, TC3 open	16	21	24	
Temperature Coefficient $(T_J > DT_0)$		TC1 GND, TC2 GND, TC3 open	24	32	36	
(13 / 210)		TC1 GND, TC2 GND, TC3 GND	36	48	54	
	TC _{LOW} -	TC1 open, TC2 open, TC3 open	-18	-16	-12	μΑ/°C
Low-Current Negative		TC1 GND, TC2 open, TC3 open	-24	-21	-16	
Temperature Coefficient $(T_J < DT_0)$		TC1 GND, TC2 GND, TC3 open	-36	-32	-24	
(.0 (2 .0)		TC1 GND, TC2 GND, TC3 GND	-54	-47	-36	
Width of Temperature-Stable Low-Current Region	Tw		38	45	52	°C
	DT ₀	DT01 open, DT02 open	31.5	36	41.5	°C
Center of Temperature-Stable		DT01 V _{CC} , DT02 open	44	49	54	
Low-Current Region		DT01 open, DT02 V _{CC}	56	61	66	
		DT01 V _{CC} , DT02 V _{CC}	68.5	74	78.5	
Modulation-Current Temperature Coefficient	TC _{MOD}	Relative to I _{MOD} at T _J = +25°C	0.311	0.38	0.471	%/°C

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +3.0 \text{V to } +5.25 \text{V}, T_J = -40 ^{\circ}\text{C} \text{ to } +140 ^{\circ}\text{C}. \text{ Typical values are at } V_{CC} = +5.0 \text{V} \text{ and } T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.})$

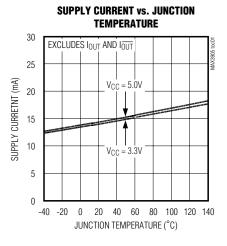
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
		MOD1 open, MOD2 open	2.84	3.01	3.22	
Modulation Current at T _J = +25°C	I _{MOD}	MOD1 V _{CC} , MOD2 open	3.44	3.65	3.88	A
		MOD1 open, MOD2 V _{CC}	4.03	4.28	4.55	mA _
		MOD1 V _{CC} , MOD2 V _{CC}	4.62	4.91	5.22	
Modulation Current in Low-Power Mode	ILP	Relative to programmed nominal, T _J = +25°C	40	50	60	%
Modulation Switching Time	t _r , t _f	20% to 80% (Note 1)		0.2	0.5	ns
Pulse-Width Variation	PWV	(Notes 1, 2)	0.97		1.03	UI
Pulse-Width Distortion	PWD	(Notes 1, 2)	-0.02		+0.02	UI
Data-Dependent Jitter	DDJ	(Notes 1, 2)		0.004	0.01	UI
Uncorrelated Jitter	UJ	(Notes 1, 2)			0.001	UI
Deterministic Jitter	DJ	K28.5 pattern at 125Mbps (Notes 1, 3)		85	200	psp-p
Random Jitter	RJ	1-0 pattern differential input (Note 1)		3	11	psRMS
IN_TTL DATA INPUT						
Input Low	V _{INL}		-0.03		+0.80	V
Input High	VINH		2.0		V _{CC} + 0.3	V
Input Resistance			4	5.75		kΩ
Input Capacitance		(Note 1)		0.3	2	рF
DIFFERENTIAL DATA INPUT						
Differential-Input Sensitivity				25	200	mV _{P-P}
Differential-Input Overload			1860			mV _{P-P}
Differential-Input Resistance				8		kΩ
3DB INPUT						
Input Threshold Voltage				1.5		V
2DB Input Voltage		Normal mode	2.0			V
3DB Input Voltage		Low-power mode			0.8	V
Diagnostia Pagistor	RGAINN	V _{CC} > 4.75V, normal mode			16	kΩ
Diagnostic Resistor	RGAINL	V _{CC} > 4.75V, low-power mode	29			K22
DATA SQUELCH						
Output Current While Squelched	loff	No input data		3	50	μΑ
Time to Squelch	tsq	(Note 1)	1	8	25	μs
Time to Resume from Squelch State	t _{RS}	(Note 1)		0.1	5	μs
ESD PROTECTION						
IN+, IN-, TTL IN, 3DB		Human Body Model	±4			kV
1 + , 1 - ,		Machine Model	±400			V

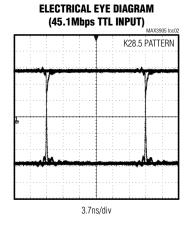
- **Note 1:** These specifications are guaranteed by design and characterization.
- **Note 2:** Pulse-width variation, pulse-width distortion, data-dependent jitter, and uncorrelated jitter are measured at 45Mbps per MOST specification of physical Layer (revision 1.1).
- **Note 3:** Deterministic jitter is measured with a K28.5 pattern (0011 1110 1011 0000 0101). Deterministic jitter is the peak-to-peak deviation from ideal time crossings, measured at the 50% crossings of the output. Differential data applied to input.

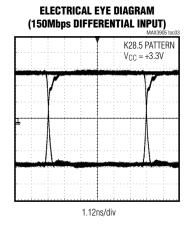


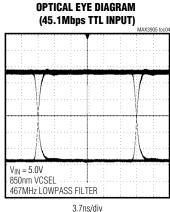
Typical Operating Characteristics

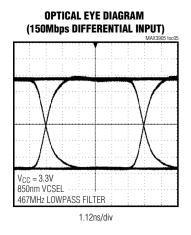
 $(LOW[1, 2] = [GND, open], MOD[1, 2] = [open, V_{CC}], DT0[1, 2] = [open, open], TC[1, 2, 3] = [GND, GND, open], T_A = +25$ °C, unless otherwise noted.)

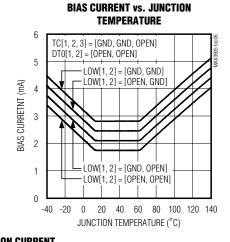


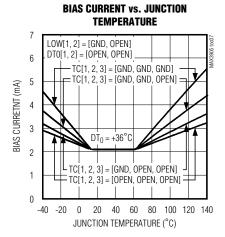


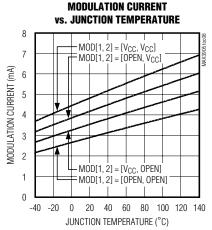






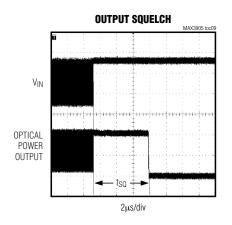


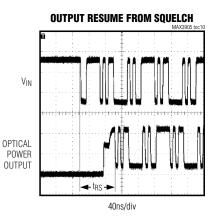


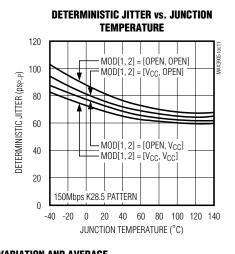


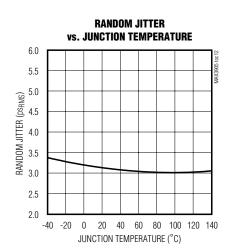
Typical Operating Characteristics (continued)

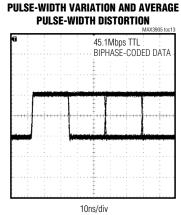
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Pad Description

PAD	NAME	FUNCTION
1, 20, 26	VEE	Circuit Ground
2	DIFF	Differential-Input Data Enable. Leave open to enable the TTL data input, or connect to ground to enable the differential data input.
3	IN_TTL	Single-Ended Data Input, TTL. Compatible with SP1 automotive network interface. This input is active when DIFF is left open.
4, 5, 6	N.C.	No Connection
7	IN+	Positive Differential-Data Input, PECL- or LVDS-Compatible. This high-impedance input is internally biased to approximately 1.4V and requires an external termination resistor and an AC-coupling capacitor. It is active when DIFF is connected to ground.
8	TEMPSENS	Junction Temperature Sensor. Analog output corresponding to the junction temperature of the die. Leave open for normal use.
9	IN-	Negative Differential-Data Input, PECL- or LVDS-Compatible. This high-impedance input is internally biased to approximately 1.4V and requires an external termination resistor and an AC-coupling capacitor. It is active when DIFF is connected to ground.
10, 15	Vcc	Power Supply
11	DT01	Driver T ₀ Programming Input. Sets the center temperature of lowest bias current. Connect to V _{CC} or leave open.
12	DT02	Driver T ₀ Programming Input. Sets the center temperature of lowest bias current. Connect to V _{CC} or leave open.
13	MOD2	Modulation-Current Programming Input. Sets the modulation-current amplitude. Connect to V _{CC} or leave open.
14	MOD1	Modulation-Current Programming Input. Sets the modulation-current amplitude. Connect to V _{CC} or leave open.
16	OUT	Complementary Data Output. Connect to VCC or VCSEL anode.
17	OUT	Data Output. Connect to VCSEL cathode.
18	SQEN	Squelch Enable Input. Leave open to enable squelch or connect to ground to disable squelch.
19	3DB	Power-Reduction Input. Compatible with TTL. When low, 3DB activates a test mode, which reduces output power by 50%. When 3DB is high, the modulation output is normal. See the <i>Detailed Description</i> section.
21	TC1	Low-Current Temperature-Coefficient Programming Input. Sets the temperature coefficient of the bias current. Connect to GND or leave open. Do not connect to V _{CC} .
22	TC2	Low-Current Temperature-Coefficient Programming Input. Sets the temperature coefficient of the bias current. Connect to GND or leave open. Do not connect to V _{CC} .
23	TC3	Low-Current Temperature-Coefficient Programming Input. Sets the temperature coefficient of the bias current. Connect to GND or leave open. Do not connect to V _{CC} .
24	LOW1	Low-Current Programming Input. Sets the VCSEL-low (bias) current at the temperature set by the DT0 pins. Connect to GND or leave open. Do not connect to V _{CC} .
25	LOW2	Low-Current Programming Input. Sets the VCSEL-low (bias) current at the temperature set by the DT0 pins. Connect to GND or leave open. Do not connect to V _{CC} .

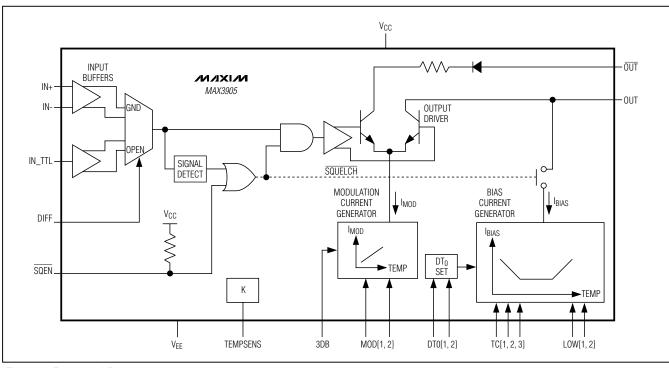


Figure 1. Functional Diagram

Detailed Description

The MAX3905 is comprised of a differential LVDS- or PECL-compatible input buffer, a TTL-compatible input buffer, signal detection, DT₀ set block, modulation-current generator, bias-current generator, and output driver (Figure 1). The device implements temperature compensation in the bias and modulation that can be customized to accommodate the variation of VCSEL properties with process and temperature. See Figure 2 and Table 1 for driver current and temperature coefficient definitions.

Input Buffers

The MAX3905 has two input buffers, one for TTL-compatible DC-coupled input data, and the other for AC-coupled, differential LVDS or PECL input data. The differential input is relatively high impedance. This allows external resistors to be configured in several ways to meet the AC- and DC-termination requirements of LVDS or PECL.

The active data input buffer is set by the DIFF input. To select the single-ended TTL input, leave DIFF open. To select the differential input, connect DIFF to ground.

When using the differential input buffer, input noise can be sufficient to prevent normal operation of the squelch function. A small offset on the input ensures proper functioning of the squelch feature. A $1M\Omega$ resistor from IN- to ground or VCC creates a 7mV offset.

Signal Detection and Data Squelch

When no data transitions are present at the input, the signal detection issues a squelch signal to the bias and modulation current, disabling the VCSEL output. This ensures that the receiver IC can easily detect the difference between transmitter on and transmitter off. The squelch function is enabled when $\overline{\text{SQEN}}$ is left unconnected. The squelch function can be disabled by connecting $\overline{\text{SQEN}}$ to ground.

With squelch enabled, the delay of the squelch function is suitable for use with biphase-encoded data (maximum of three consecutive identical digits (CIDs)) or 8B-/10B-encoded data (maximum five CIDs). To use the MAX3905 with scrambled data, disable the squelch function.

DT₀ Set Block

Inputs DT01 and DT02 are the 2-bit control of the center of the temperature-stable region, DT0. The temperature set by DT0[1, 2] should correspond to the T0 of the VCSEL. Connect DT01 or DT02 to VCC to set the bit high, or leave open to set the bit low.

The typical DT₀ can be calculated by:

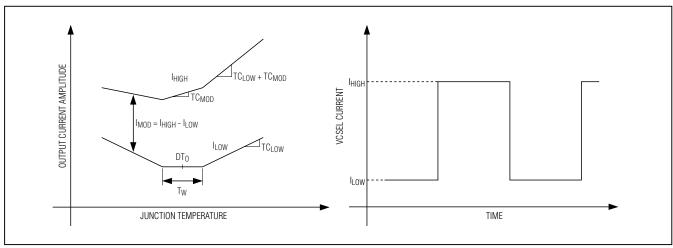


Figure 2. Driver Current and Temperature Coefficient Definitions

Table 1. Driver Current and Temperature Coefficient Definitions

PARAMETER	DESCRIPTION		
ILOW	Total VCSEL current when the data input is logic-low.		
Інідн	Total VCSEL current when the data input is logic-high.		
IMOD	lhigh - Ilow.		
DT ₀	The center of the temperature-stable low-current region (T _W). DT_0 roughly corresponds to T_0 of the VCSEL.		
I _{DT0}	I_{LOW} at $T_J = DT_0$.		
Tw	The size (in °C) of the region where no temperature coefficient is applied to I _{LOW} .		
TC _{MOD}	The temperature coefficient applied to I _{MOD} .		
TC _{LOW}	The temperature coefficient applied to I_{LOW} . This coefficient is negative below DT_0 - $T_W/2$ and positive above DT_0 + $T_W/2$.		
IOFF	Total VCSEL current while squelched.		

 $DT_0 \approx [36 + 13(DT01) + 25(DT02)]^{\circ}C$

where DT0[1, 2] = 1 when bonded to V_{CC} ; DT0[1, 2] = 0 when left open.

Modulation-Current Generator

The modulation-current generator provides wirebond-selectable current amplitude with temperature compensation. The temperature coefficient (TCMOD) compensates for the slope-efficiency change of the VCSEL over temperature. The modulation current is set with inputs MOD1 and MOD2. Connect MOD1 or MOD2 to V_{CC} to set the bit high, and leave open to set the bit low.

The typical modulation current at +25°C can be calculated by:

 $I_{MOD} \approx [3.01 + (0.64 \times MOD1) + (1.27 \times MOD2)]mA$ where MOD[1, 2] = 1 when bonded to V_{CC}; MOD [1, 2] = 0 when left open.

Power Reduction

The power-reduction feature is useful for in-system test and diagnostics. When the 3DB input is low, the modulation current is reduced by 50%. When 3DB is high or VCC, the modulation output is normal.

For compatibility with 5V POF transmitters, the power mode can be set by connecting a resistor from 3DB to VCC. A resistor RGAIN < RGAINN sets the normal power mode, while RGAIN > RGAINL sets the low-power mode.

Bias-Current Generator

The bias-current generator provides a current that closely tracks the VCSEL properties with temperature. This current is summed with the modulation current at the OUT pad. The bias current at $T_J = DT_0$ is

programmed by the LOW1 and LOW2 inputs. Connect LOW1 or LOW2 to ground to set the bit high, and leave open to set the bit low. Do not connect LOW1 or LOW2 to $V_{\rm CC}$.

The typical low current at $T_J = DT_0$ can be calculated by: $I_{I,OW} \approx [1.8 + (0.37 \times LOW1) + (0.73 \times LOW2)]mA$

where, LOW[1, 2] = 1 when bonded to ground; LOW[1, 2] = 0 when left open.

The temperature coefficient of the bias current is programmed by the TC1, TC2, and TC3 inputs. Connect TC1, TC2, or TC3 to ground to set the bit high, and leave open to set the bit low. Do not connect TC1, TC2, or TC3 to VCC.

The typical temperature coefficient of the bias current can be calculated by:

TCLOW
$$\approx$$
 [16 + (5 x TC1) + (11 x TC2) + (16 x TC3)] μ A/°C

where, TC[1, 2, 3] = 1 when bonded to ground; TC[1, 2, 3] = 0 when left open.

Junction-Temperature Sensing

A temperature sensor is incorporated into the MAX3905 to aid in evaluation of thermal performance. The TEMPSENS voltage is proportional to the die junction temperature (approximately -1.39mV per °C). The temperature of the die can be estimated as:

$$T(^{\circ}C) \approx 597^{\circ}C - V_{TEMPSENS} (mV) \times \frac{0.72^{\circ}C}{1mV}$$

Output Driver

The $\overline{\text{OUT}}$ pad connects directly to the VCSEL cathode. The $\overline{\text{OUT}}$ pad must be connected to the VCSEL anode or to V_{CC}. The minimum instantaneous voltage on the OUT pad is 0.9V.

Applications Information

Additional Design Assistance

For more information and design assistance, refer to Maxim Design Note HFDN-32.0: *Output Current Calculator for the MAX3905*.

Layout Considerations

Load inductance on OUT and OUT should be matched within 1.5nH to minimize both jitter and supply noise generation.

Wire Bonding

For high-current density and reliable operation, the MAX3905 uses gold metalization. For best results, use gold-wire ball-bonding techniques. Exercise caution when wedge bonding. Die size is 1.52mm x 1.52mm (60 mils x 60 mils), and die thickness is 300µm (12 mils). The bond-pad passivation opening is 93µm x 93µm and bond-pad metal thickness is 1.2µm. Refer to Maxim Application Note HFAN-08.0.1: *Understanding Bonding Coordinates and Physical Die Size* for additional information on bondpad coordinates. Do not attempt to bond to the laser trim target.

Laser Safety and IEC 825

Using the MAX3905 VCSEL driver alone does not ensure that a transmitter design is compliant with IEC 825. The entire transmitter circuit and component selections must be considered. Determine the level of fault tolerance required by each application, and recognize that Maxim products are not designed or authorized for use as components in systems intended for surgical implant into the body, for applications intended to support or sustain life, or for any other application where the failure of a Maxim product could create a situation where personal injury or death may occur.

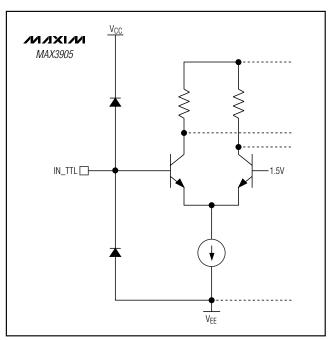


Figure 3. IN_TTL Equivalent Input Structure

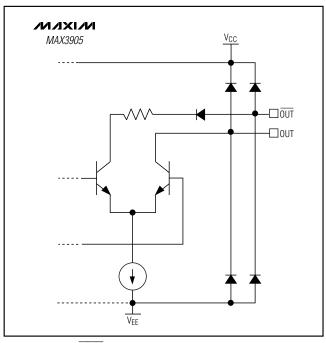


Figure 5. OUT/OUT Equivalent Output Structure

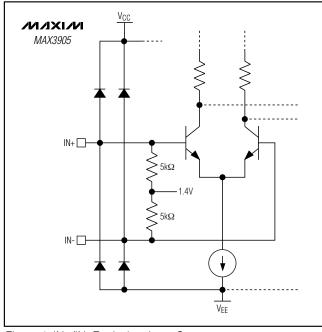


Figure 4. IN+/IN- Equivalent Input Structure

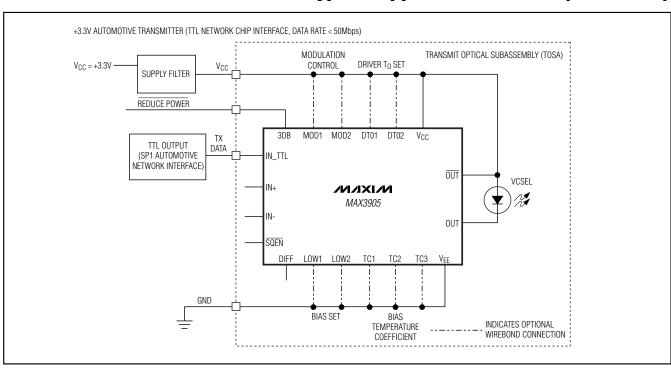
_Chip Information

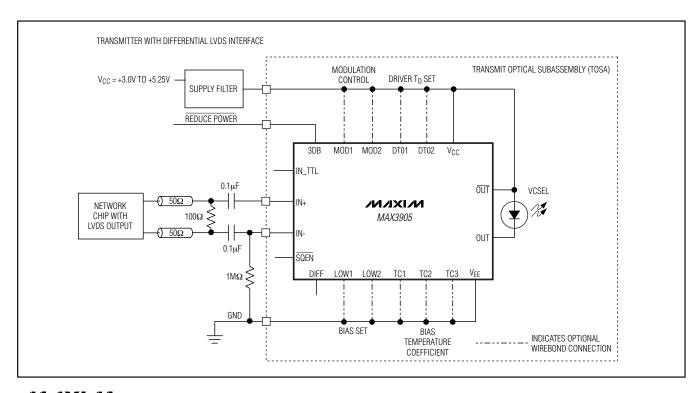
TRANSISTOR COUNT: 985
PROCESS: Silicon Bipolar GST-2
SUBSTRATE: Connected to VEE

DIE SIZE: 1.52mm x 1.52mm (60mils x 60mils)

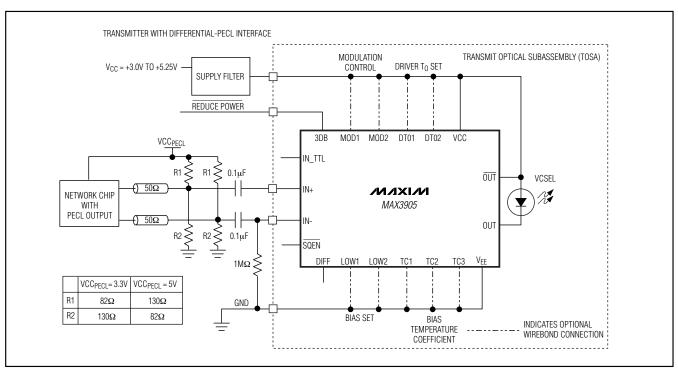
DIE THICKNESS: 300µm (12mils)

Typical Application Circuits (continued)





Typical Application Circuits (continued)



Bonding Coordinates

PAD	PAD NAME	COORDINATES (µm)		
FAU	PAD NAME	Х	Υ	
1	VEE	46.6	1285.9	
2	DIFF	46.6	1134.7	
3	IN_TTL	46.6	983.5	
4	N.C.	46.6	832.3	
5	N.C	46.6	511	
6	N.C	46.6	359.8	
7	IN+	46.6	208.6	
8*	TEMPSENS	46.6	46.6	
9	IN-	262.6	46.6	
10	Vcc	791.8	46.6	
11	DT01	956.5	46.6	
12	DT02	1121.2	46.6	
13	MOD2	1285.9	46.6	

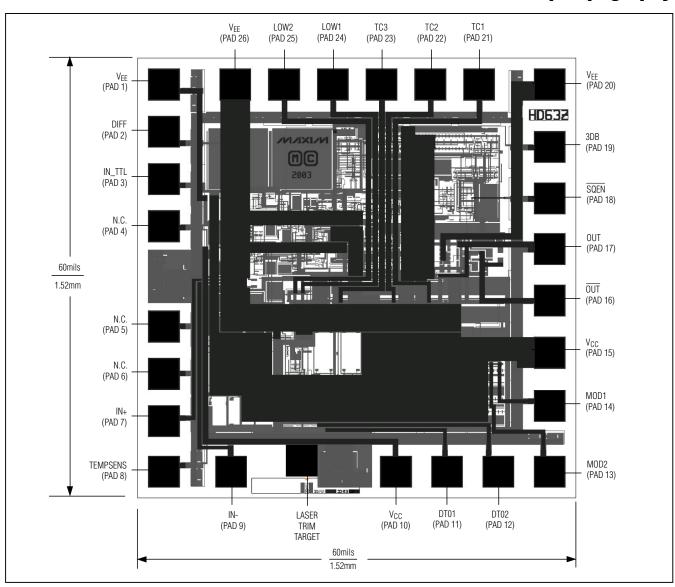
PAD	PAD NAME	COORDINATES (µm)		
PAD	PAD NAME	Х	Υ	
14	MOD1	1285.9	257.2	
15	Vcc	1285.9	427.3	
16	OUT	1285.9	594.7	
17	OUT	1285.9	759.4	
18	SQEN	1285.9	921.4	
19	3DB	1285.9	1086.1	
20	VEE	1285.9	1285.9	
21	TC1	1059.1	1285.9	
22	TC2	902.5	1285.9	
23	TC3	745.9	1285.9	
24	LOW1	589.3	1285.9	
25	LOW2	432.7	1285.9	
26	VEE	276.1	1285.9	

Coordinates are for the center of the pad.

Coordinate 0,0 is the lower left corner of the passivation opening for pad 8.

^{*}Index pad. Orient the die with this pad in the lower-left corner.

Chip Topography



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